Case 10662302

S13557 U USPT,USOC,EPAB 257/E21.582 and semiconductor$2 and interconnect$3 and (via$2 or hole$2) and siv$3 and (buffer$3 or insulat$3 or seperat$3) near (interconnect$3 or metal or layer) and (siv or (stress near induc$3 near void$2))

S13556 U USPT,USOC,EPAB 257/E23.145 and semiconductor$2 and interconnect$3 and (via$2 or hole$2) and siv$3 and (buffer$3 or insulat$3 or seperat$3) near (interconnect$3 or metal or layer) and (siv or (stress near induc$3 near void$2))

S13555 U USPT,USOC,EPAB 257/E23.161 and semiconductor$2 and interconnect$3 and (via$2 or hole$2) and siv$3 and (buffer$3 or insulat$3 or seperat$3) near (interconnect$3 or metal or layer) and (siv or (stress near induc$3 near void$2))

S13554 U USPT,USOC,EPAB 257/E21.582

S13553 U USPT,USOC,EPAB 257/E23.582

S13552 U USPT,USOC,EPAB 257/E23.145

S13551 U USPT 257/E23.161

S13550 U USPT E23.161.CCLS.

S13549 U USPT 257/E23.161.CCLS.

S13548 U USPT 427/96,337,344,378,380,397.7,384,343.CCLS. and semiconductor$2 and interconnect$3 and (via$2 or hole$2) and siv$3 and (buffer$3 or insulat$3 or seperat$3) near (interconnect$3 or metal or layer) and (siv or (stress near induc$3 near void$2))

S13547 U USPT 427/96,337,344,378,380,397.7,384,343.CCLS.

S13546 U USPT 257/758,757,767,774,773,775,781,632642,637,537,759.CCLS. and semiconductor$2 and interconnect$3 and (via$2 or hole$2) and siv$3 and (buffer$3 or insulat$3 or seperat$3) near (interconnect$3 or metal or layer) and (siv or (stress near induc$3 near void$2))

S13545 U USPT   257/758,757,767,774,773,775,781,632,642,637,537,759.CCLS.

S13544 U USPT   257/758,757,767,774,E23.161,E23.145,E21.582,773,775,781,632.CCLS.

S13543 U USPT   438/734,618,622,687,637,672,926,781,763,778,622,758.ccls. and
                     semiconductor$2 and interconnect$3 and (via$2 or hole$2) and siv$3
                     and (buffer$3 or insulat$3 or seperat$3) near (interconnect$3 or metal or
                     layer) and (siv or (stress near induc$3 near void$2))
S13542 U USPT   438/734,618,622,687,637,672,926,781,763,778,622,758.ccls.

S13541 U USPT   (semiconductor$2 and interconnect$3 and (via$2 or hole$2)and siv$3
                     and (buffer$3 or insulat$3 or seperat$3) near (interconnect$3 or metal or
                     layer) and (siv or (stress near induc$3 near void$2))) and siv
S13540 U USPT   (semiconductor$2 and interconnect$3 and (via$2 or hole$2)and siv$3
                     and (buffer$3 or insulat$3 or seperat$3) near (interconnect$3 or metal or
                     layer) and (siv or (stress near induc$3 near void$2))) and void$3

ID			Query	Date
S13265 U USPT			(siv or (stress near induc$3 near void$2)) and metal$2 and buffer$3 and interconnect$3	2005-01-04 00:39:47
S13264 U USPT			(siv or (stress near induc$3 near void$2)) and metal$2 and buffer$3	2005-01-04 00:39:13
S13263 U USPT			(siv or (stress near induc$3 near void$2))	2005-01-04 00:38:32
S13262 U USPT			semiconductor$2 and interconnect$3 and (via$2 or hole$2)and siv$3 and (buffer$3 or insulat$3 or seperat$3) near (interconnect$3 or metal or layer) and (siv or (stress near induc$3 near void$2))	2005-01-04 00:38:13
S13261 U USPT			semiconductor$2 and interconnect$3 and (via$2 or hole$2)and siv$3 and (buffer$3 or insulat$3 or seperat$3) near (interconnect$3 or metal or layer) and (siv$1 or (stress near(induc$3 or void$2)))	2005-01-04 00:36:01
S13260 U USPT			semiconductor$2 and interconnect$3 and (via$2 or hole$2)and siv$3 and (buffer$3 or insulat$3 or seperat$3) near (interconnect$3 or metal or layer) and (siv$2 or (stress near(induc$3 or void$2))) and metal$3	2005-01-04 00:21:32

S13259 U USPT	semiconductor$2 and interconnect$3 and (via$2 or hole$2)and siv$3 and (buffer$3 or insulat$3 or seperat$3) near (interconnect$3 or metal or layer) and (siv$2 or (stress near(induc$3 or void$2)))	2005-01-04 00:19:52
S13258 U USPT	semiconductor$2 and interconnect$3 and (via$2 or hole$2)and siv$3 and (buffer$3 or insulat$3 or seperat$3) near (interconnect$3 or metal or layer)	2005-01-04 00:17:41
S13257 U USPT	semiconductor$2 and interconnect$3 and (via$2 or hole$2)and siv$3 and (buffer$3 or insulat$3) near (interconnect$3 or metal or layer)	2005-01-04 00:16:38
S13256 U USPT	semiconductor$2 and interconnect$3 and (via$2 or hole$2)and siv$3 and buffer$3	2005-01-04 00:15:36
S13255 U USPT	semiconductor$2 and interconnect$3 and (via$2 or hole$2)and siv$3	2005-01-04 00:15:09
S13254 U USPT	semiconductor$2 and interconnect$3 and (via$2 or hole$2) and (first or second or two) near interconnect$3 and siv$3 and buffer$3	2005-01-03 23:58:44
S13253 U USPT	semiconductor$2 and interconnect$3 and (via$2 or hole$2) and (first or second or two) near interconnect$3 and siv$3	2005-01-03 23:52:12
S13252 U USPT	semiconductor$2 and interconnect$3 and (via$2 or hole$2) and (first or second or two) near interconnect$3	2005-01-03 23:43:17
S13251 U USPT	semiconductor near process and (thermopile near (sensor$2 or detector$2) or infared$2 near (sensor$2 or detector$2))	2005-01-03 14:29:42
S13250 U USPT	semiconductor near process	2005-01-03 14:29:13